

SANYO	No.1390D	2SA1353/2SC3417
	PNP/NPN Epitaxial Planar Silicon Transistors Ultrahigh-Definition CRT Display Video Output Applications	

Applications

- Ultrahigh-definition CRT display.
- Color TV chroma output, high-voltage driver applications

Features

- High breakdown voltage : $V_{CE0} \geq 300V$.
- Excellent high frequency characteristics : $C_{re} = 1.8pF$ (typ).
- Adoption of MBIT process.

() : 2SA1353

Absolute Maximum Ratings at $T_a = 25^\circ C$

			unit
Collector-to-Base Voltage	V_{CB0}	(-)300	V
Collector-to-Emitter Voltage	V_{CE0}	(-)300	V
Emitter-to-Base Voltage	V_{EB0}	(-)5	V
Collector Current	I_C	(-)100	mA
Collector Current (Pulse)	I_{CP}	(-)200	mA
Collector Dissipation	P_C	1.2	W
		7	W
Junction Temperature	T_j	150	$^\circ C$
Storage Temperature	T_{stg}	- 55 to + 150	$^\circ C$

$T_c = 25^\circ C$

Electrical Characteristics at $T_a = 25^\circ C$

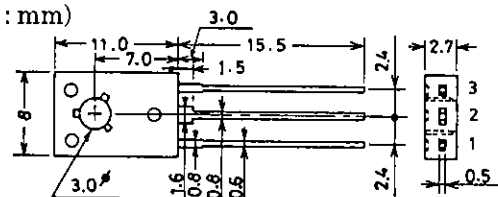
			min	typ	max	unit
Collector Cutoff Current	I_{CBO}	$V_{CB} = (-)200V, I_E = 0$			(-)0.1	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB} = (-)4V, I_C = 0$			(-)0.1	μA
DC Current Gain	h_{FE}	$V_{CE} = (-)10V, I_C = (-)10mA$	40		320	
Gain Bandwidth Product	f_T	$V_{CE} = (-)30V, I_C = (-)10mA$		70		MHz
C-E Saturation Voltage	$V_{CE(sat)}$	$I_C = (-)20mA, I_B = (-)2mA$			(-)0.6	V
B-E Saturation Voltage	$V_{BE(sat)}$	$I_C = (-)20mA, I_B = (-)2mA$			(-)1.0	V
C-B Breakdown Voltage	$V_{(BR)CBO}$	$I_C = (-)10\mu A, I_E = 0$	(-)300			V
C-E Breakdown Voltage	$V_{(BR)CEO}$	$I_C = (-)1mA, R_{BE} = \infty$	(-)300			V
E-B Breakdown Voltage	$V_{(BR)EBO}$	$I_E = (-)10\mu A, I_C = 0$	(-)5			V
Output Capacitance	C_{ob}	$V_{CB} = (-)30V, f = 1MHz$		2.6		pF
				(3.1)		pF
Reverse Transfer Capacitance	C_{re}	$V_{CB} = (-)30V, f = 1MHz$		1.8		pF
				(2.3)		pF

※ : The 2SA1353/2SC3417 are classified by 10mA h_{FE} as follows :

40	C	80	60	D	120	100	E	200	160	F	320
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Package Dimensions 2009B

(unit : mm)



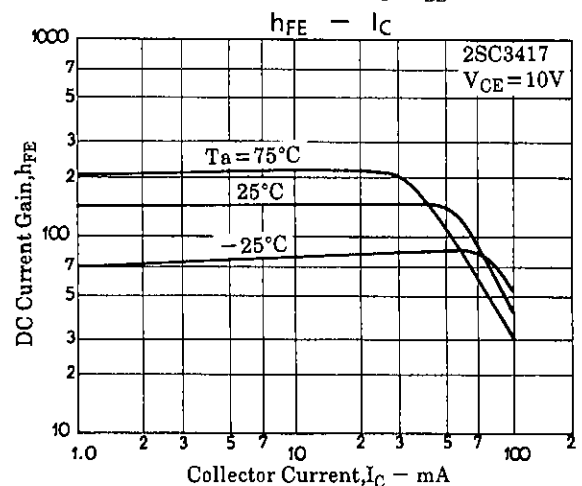
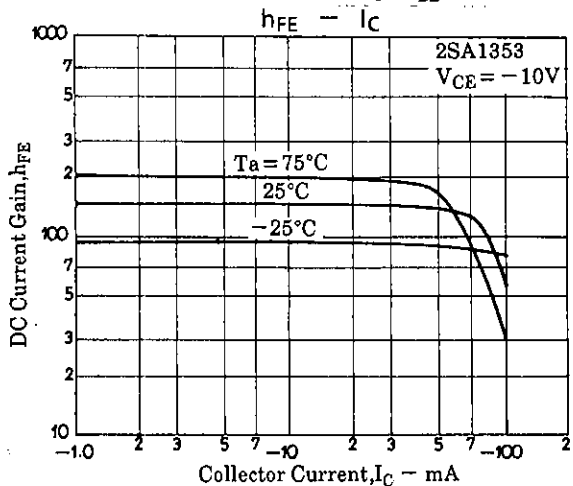
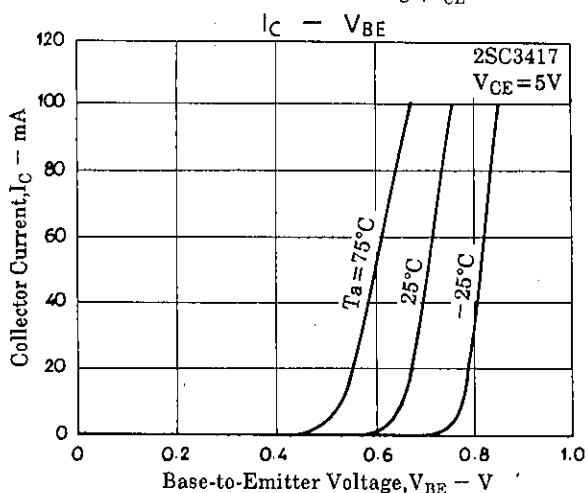
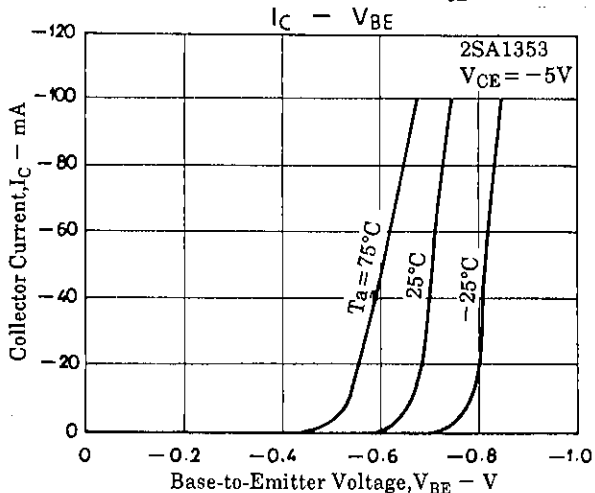
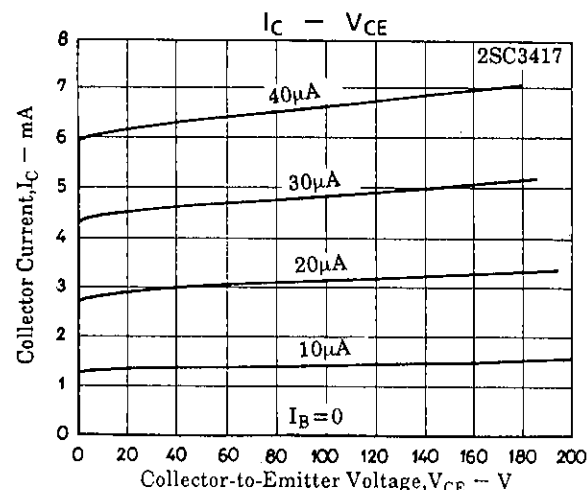
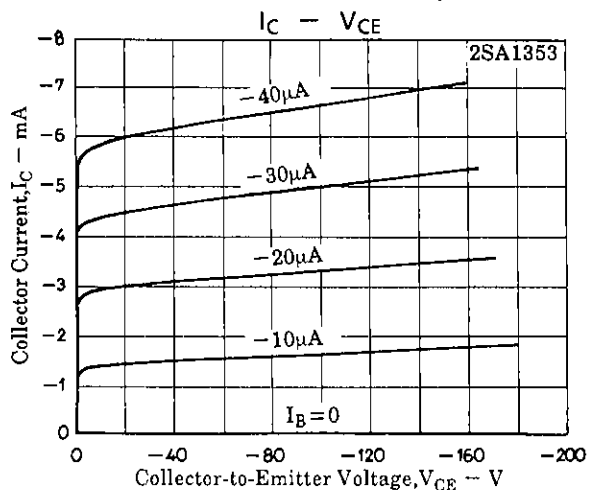
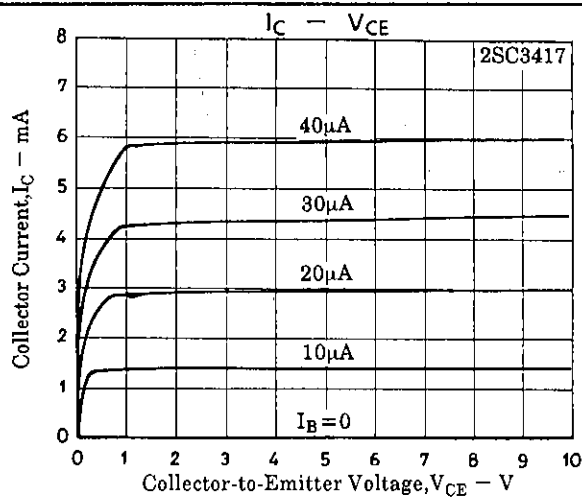
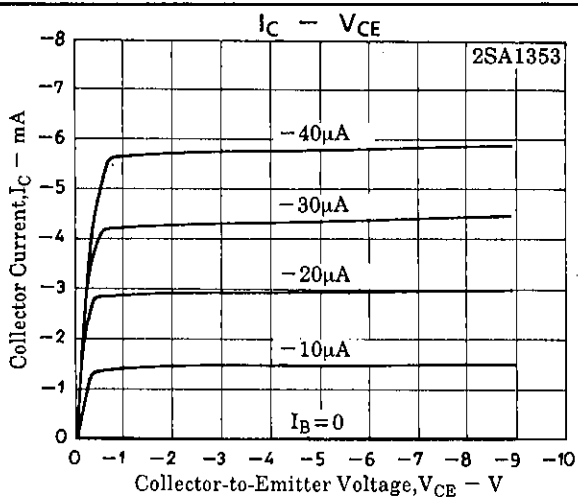
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- 1 : Emitter
- 2 : Collector
- 3 : Base

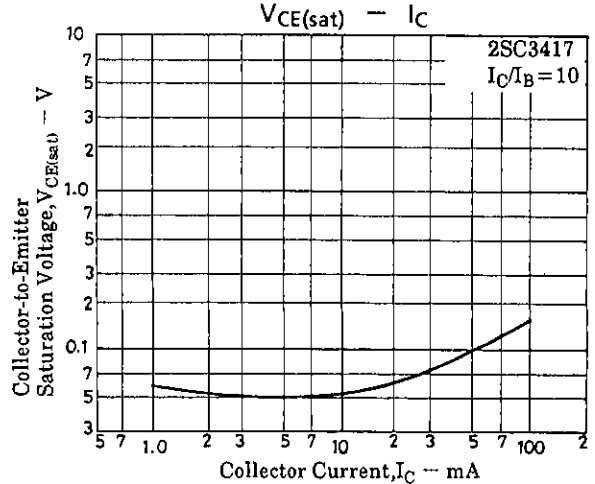
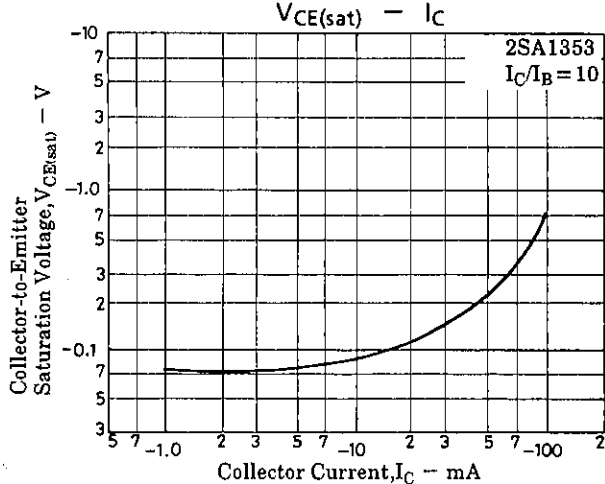
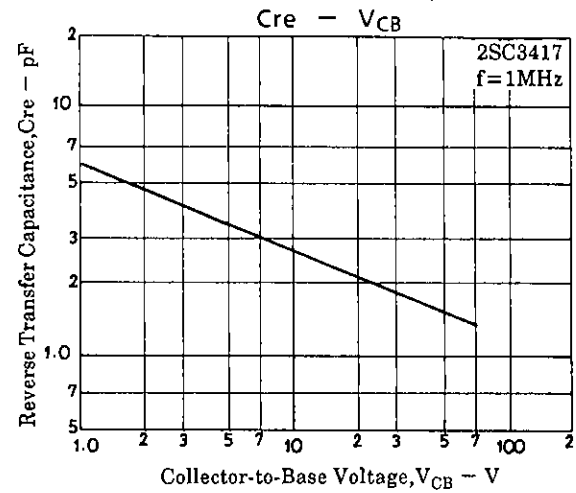
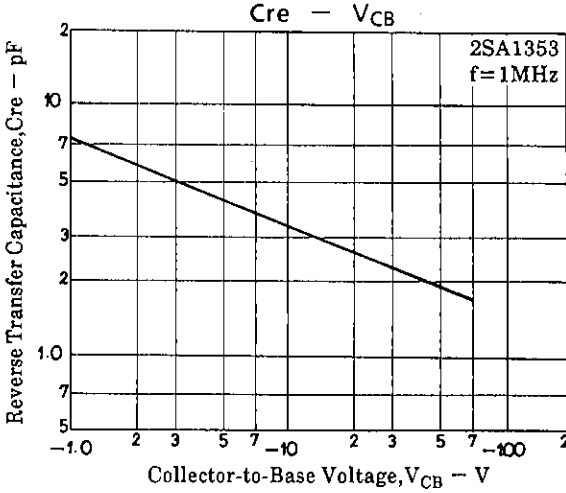
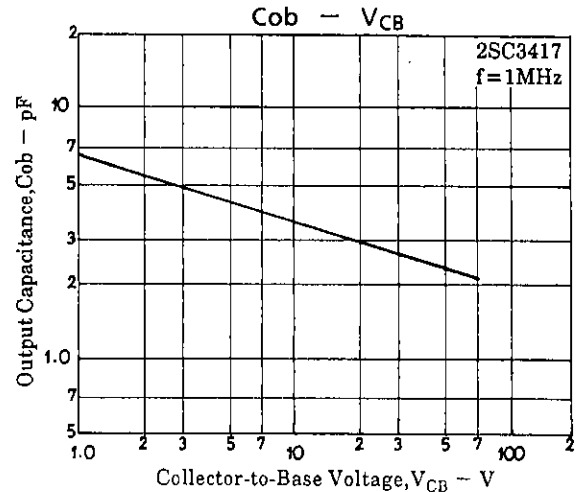
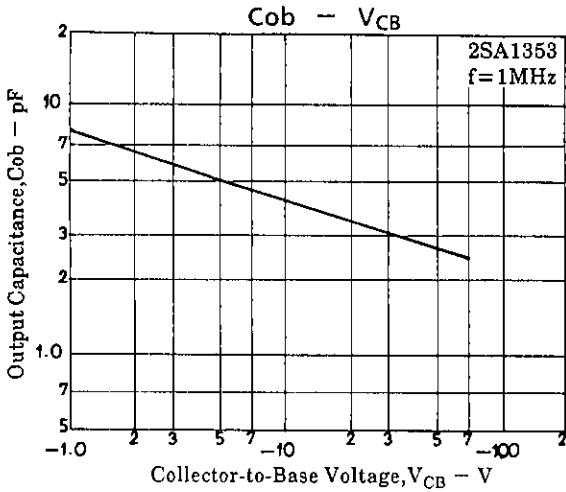
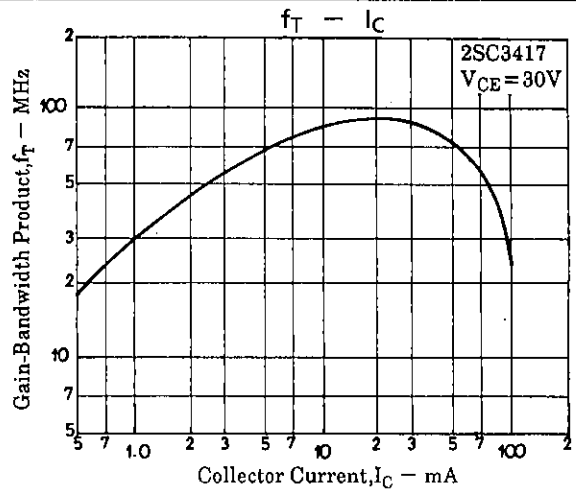
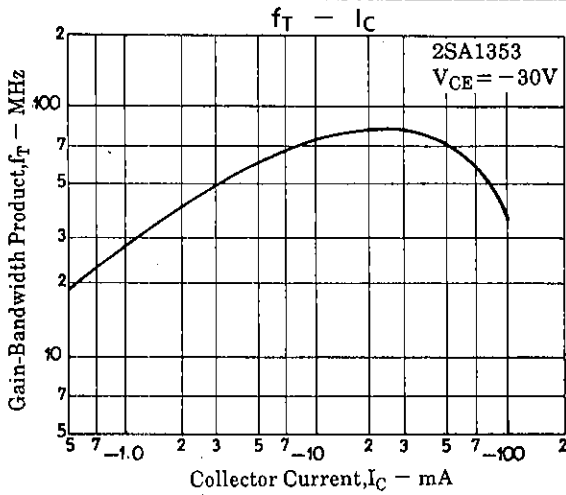
SANYO Electric Co., Ltd. Semiconductor Business Headquarters

TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110 JAPAN

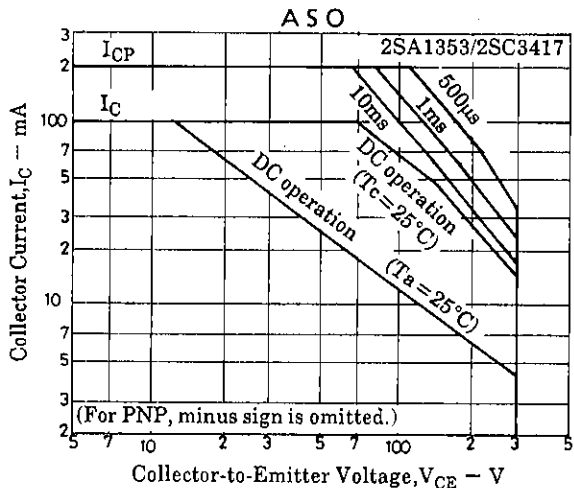
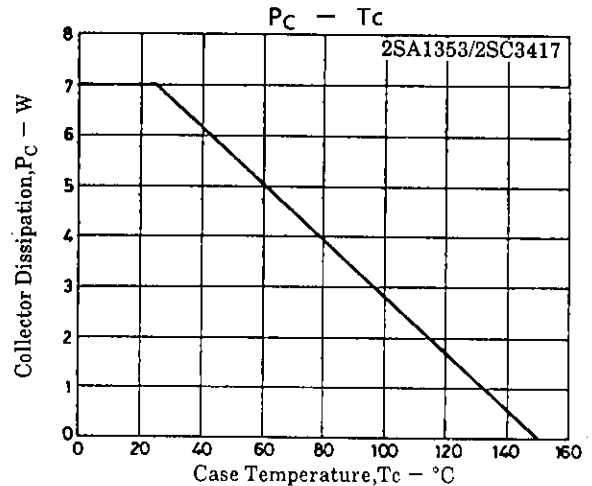
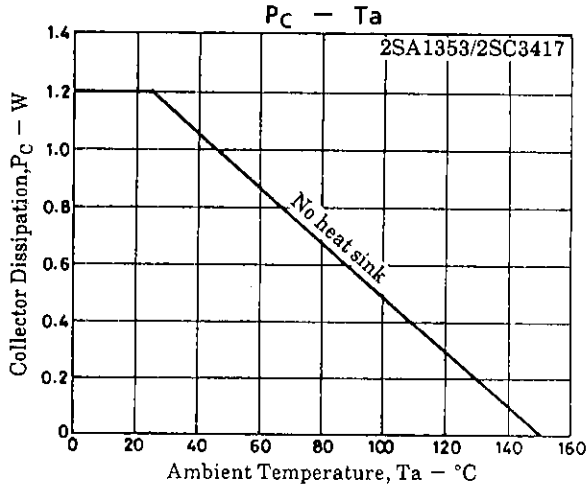
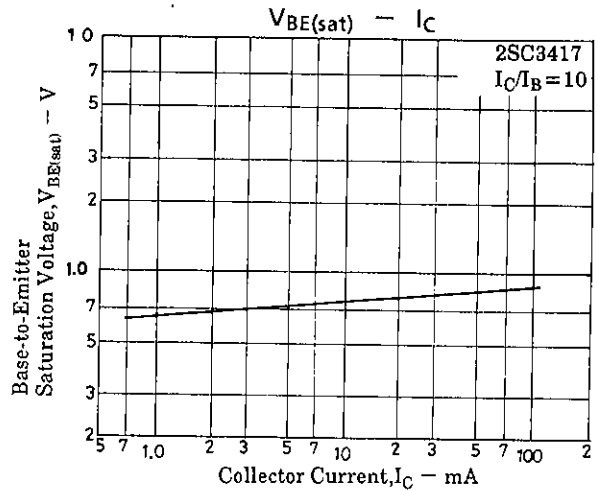
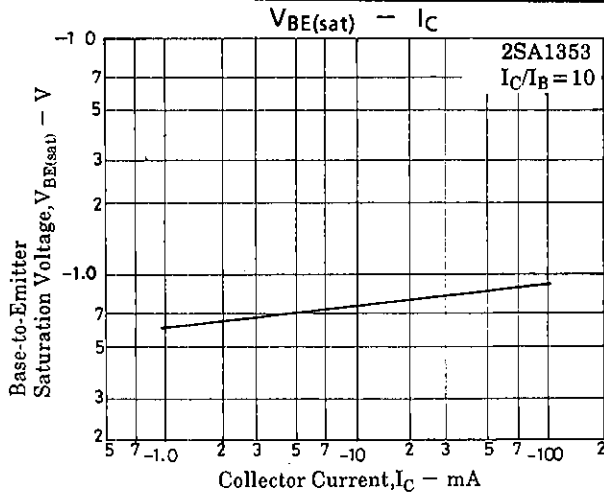
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